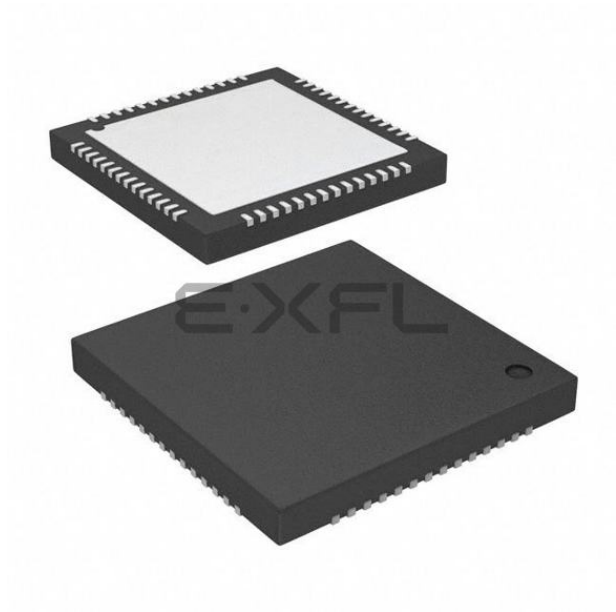

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Applications of "Embedded - Microcontrollers"

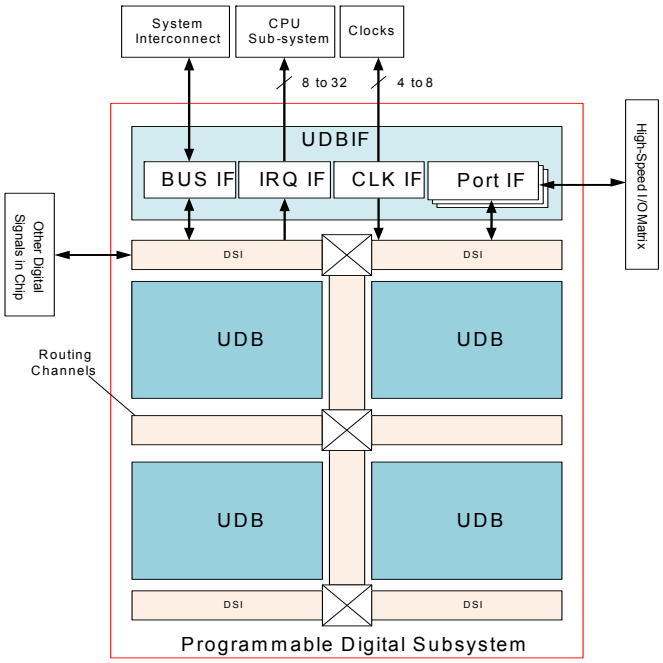
Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Bluetooth, Brown-out Detect/Reset, LVD, POR, PWM, SmartCard, SmartSense, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	56-UFQFN Exposed Pad
Supplier Device Package	56-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4247lqi-bl473

Programmable Digital

Universal Digital Blocks (UDBs) and Port Interfaces

The PSoC 4XX8 BLE 4.2 has four UDBs; the UDB array also provides a switched Digital System Interconnect (DSI) fabric that allows signals from peripherals and ports to be routed to and through the UDBs for communication and control.

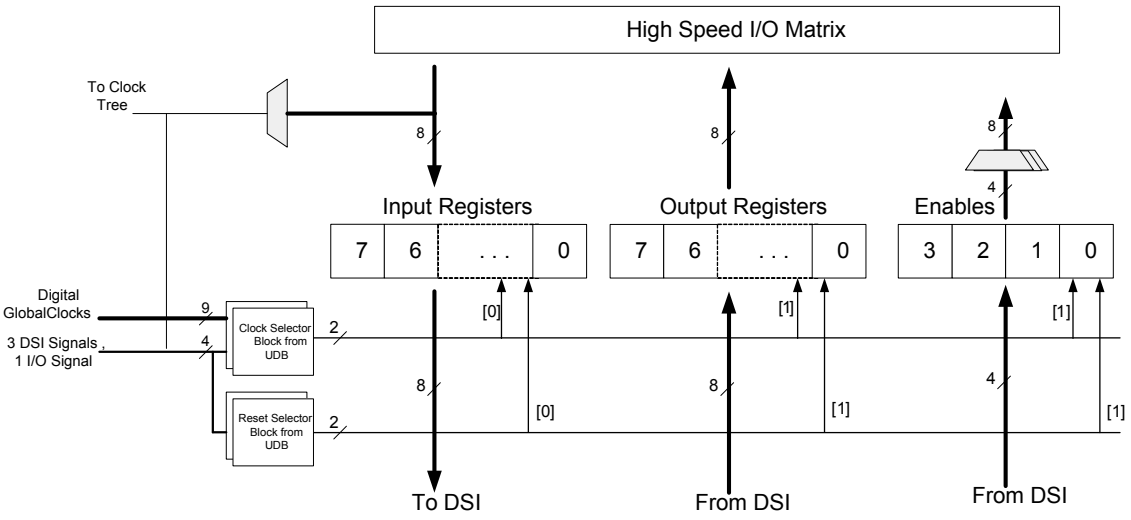
Figure 5. UDB Array



UDBs can be clocked from a clock-divider block, from a port interface (required for peripherals such as SPI), and from the DSI network directly or after synchronization.

A port interface is defined, which acts as a register that can be clocked with the same source as the PLDs inside the UDB array. This allows a faster operation because the inputs and outputs can be registered at the port interface close to the I/O pins and at the edge of the array. The port interface registers can be clocked by one of the I/Os from the same port. This allows interfaces such as SPI to operate at higher clock speeds by eliminating the delay for the port input to be routed over DSI and used to register other inputs (see Figure 6).

Figure 6. Port Interface



UDBs can generate interrupts (one UDB at a time) to the interrupt controller. UDBs retain the ability to connect to any pin on the chip through the DSI.

Fixed-Function Digital

Timer/Counter/PWM Block

The timer/counter/PWM block consists of four 16-bit counters with user-programmable period length. There is a Capture register to record the count value at the time of an event (which may be an I/O event), a period register which is used to either stop or auto-reload the counter when its count is equal to the period register, and compare registers to generate compare value signals which are used as PWM duty cycle outputs. The block also provides true and complementary outputs with programmable offset between them to allow the use as deadband programmable complementary PWM outputs. It also has a Kill input to force outputs to a predetermined state; for example, this is used in motor-drive systems when an overcurrent state is indicated and the PWMs driving the FETs need to be shut off immediately with no time for software intervention.

Serial Communication Blocks (SCB)

PSoC 4200_BL has two SCBs, each of which can implement an I^2C, UART, or SPI interface.

I^2C Mode: The hardware I^2C block implements a full multi-master and slave interface (it is capable of multimaster arbitration). This block is capable of operating at speeds of up to 1 Mbps (Fast Mode Plus) and has flexible buffering options to reduce the interrupt overhead and latency for the CPU. It also supports EzI^2C that creates a mailbox address range in the memory of PSoC 4200_BL and effectively reduces the I^2C communication to reading from and writing to an array in the memory. In addition, the block supports an 8-deep FIFO for receive and transmit, which, by increasing the time given for the CPU to read the data, greatly reduces the need for clock stretching caused by the CPU not having read the data on time. The FIFO mode is available in all channels and is very useful in the absence of DMA.

The I^2C peripheral is compatible with I^2C Standard-mode, Fast-mode, and Fast-Mode Plus devices as defined in the NXP I^2C-bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes.

SCB1 is fully compliant with Standard mode (100 kHz), Fast mode (400 kHz), and Fast-Mode Plus (1 MHz) I^2C signaling specifications when routed to GPIO pins P5[0] and P5[1], except for hot-swap capability during I^2C active communication. The remaining GPIOs do not meet the hot-swap specification (V_{DD} off; draw < 10-µA current) for Fast mode and Fast-Mode Plus, I_{OL} Spec (20 mA) for Fast-Mode Plus, hysteresis spec (0.05 V_{DD}) for Fast mode and Fast-Mode Plus, and minimum fall time spec for Fast mode and Fast-Mode Plus.

- GPIO cells, including P5.0 and P5.1, cannot be hot-swapped or powered up independent of the rest of the I^2C system.
- The GPIO pins P5.0 and P5.1 are over-voltage tolerant but cannot be hot-swapped or powered up independent of the rest of the I^2C system
- Fast-Mode Plus has an I_{OL} specification of 20 mA at a V_{OL} of 0.4 V. The GPIO cells can sink a maximum of 8 mA I_{OL} with a V_{OL} maximum of 0.6 V.
- Fast-mode and Fast-Mode Plus specify minimum Fall times, which are not met with the GPIO cell; the Slow-Strong mode can help meet this spec depending on the bus load.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows the addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated. Note that hardware handshaking is not supported. This is not commonly used and can be implemented with a UDB-based UART in the system, if required.

SPI Mode: The SPI mode supports full Motorola SPI, TI Secure Simple Pairing (SSP) (essentially adds a start pulse that is used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO for transmit and receive.

GPIO

PSoC 4200_BL has 36 GPIOs. The GPIO block implements the following:

- Eight drive strength modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL)
- Pins 0 and 1 of Port 5 are overvoltage-tolerant pins
- Individual control of input and output buffer enabling/disabling in addition to drive-strength modes
- Hold mode for latching previous state (used for retaining the I/O state in Deep Sleep and Hibernate modes)
- Selectable slew rates for dV/dt-related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width. During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix (HSIOM) is used to multiplex between various signals that may connect to an I/O pin. Pin locations for fixed-function peripherals are also fixed to reduce internal multiplexing complexity (these signals do not go through the DSI network). DSI signals are not affected by this and any pin may be routed to any UDB through the DSI network.

Data output and pin-state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4200_BL).

Pinouts

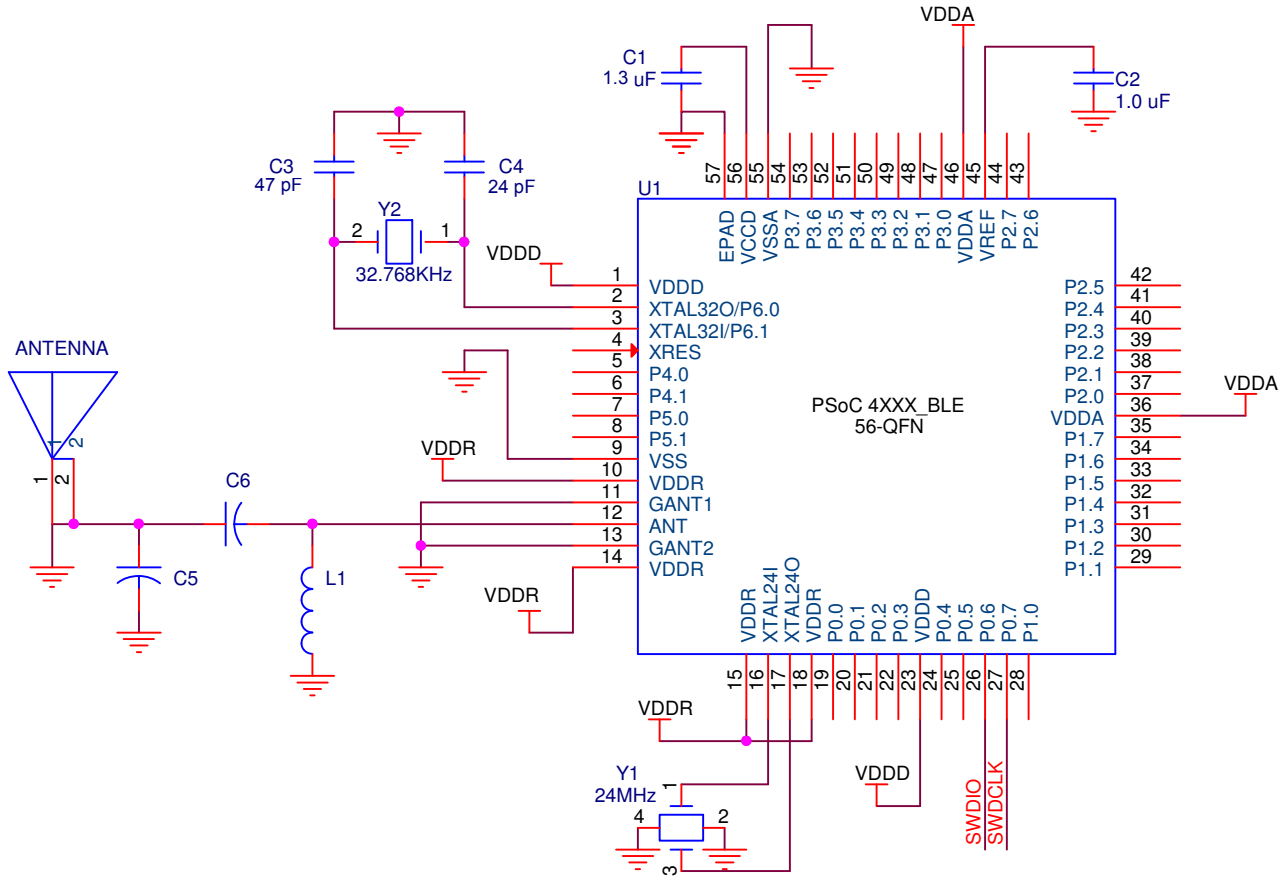
Table 1 shows the pin list for the PSoC 4200_BL device. Port 3 consists of the high-speed analog inputs for the SAR mux. All pins support CSD CapSense and analog mux bus connections.

Table 1. PSoC 4200_BL Pin List (QFN Package)

Pin	Name	Type	Description
1	VDDD	POWER	1.71-V to 5.5-V digital supply
2	XTAL32O/P6.0	CLOCK	32.768-kHz crystal
3	XTAL32I/P6.1	CLOCK	32.768-kHz crystal or external clock input
4	XRES	RESET	Reset, active LOW
5	P4.0	GPIO	Port 4 Pin 0, lcd, csd
6	P4.1	GPIO	Port 4 Pin 1, lcd, csd
7	P5.0	GPIO	Port 5 Pin 0, lcd, csd
8	P5.1	GPIO	Port 5 Pin 1, lcd, csd
9	VSSD	GROUND	Digital ground
10	VDDR	POWER	1.9-V to 5.5-V radio supply
11	GANT1	GROUND	Antenna shielding ground
12	ANT	ANTENNA	Antenna pin
13	GANT2	GROUND	Antenna shielding ground
14	VDDR	POWER	1.9-V to 5.5-V radio supply
15	VDDR	POWER	1.9-V to 5.5-V radio supply
16	XTAL24I	CLOCK	24-MHz crystal or external clock input
17	XTAL24O	CLOCK	24-MHz crystal
18	VDDR	POWER	1.9-V to 5.5-V radio supply
19	P0.0	GPIO	Port 0 Pin 0, lcd, csd
20	P0.1	GPIO	Port 0 Pin 1, lcd, csd
21	P0.2	GPIO	Port 0 Pin 2, lcd, csd
22	P0.3	GPIO	Port 0 Pin 3, lcd, csd
23	VDDD	POWER	1.71-V to 5.5-V digital supply
24	P0.4	GPIO	Port 0 Pin 4, lcd, csd
25	P0.5	GPIO	Port 0 Pin 5, lcd, csd
26	P0.6	GPIO	Port 0 Pin 6, lcd, csd
27	P0.7	GPIO	Port 0 Pin 7, lcd, csd
28	P1.0	GPIO	Port 1 Pin 0, lcd, csd
29	P1.1	GPIO	Port 1 Pin 1, lcd, csd
30	P1.2	GPIO	Port 1 Pin 2, lcd, csd
31	P1.3	GPIO	Port 1 Pin 3, lcd, csd
32	P1.4	GPIO	Port 1 Pin 4, lcd, csd
33	P1.5	GPIO	Port 1 Pin 5, lcd, csd
34	P1.6	GPIO	Port 1 Pin 6, lcd, csd
35	P1.7	GPIO	Port 1 Pin 7, lcd, csd
36	VDDA	POWER	1.71-V to 5.5-V analog supply
37	P2.0	GPIO	Port 2 Pin 0, lcd, csd
38	P2.1	GPIO	Port 2 Pin 1, lcd, csd
39	P2.2	GPIO	Port 2 Pin 2, lcd, csd

The possible pin connections are shown for all analog and digital peripherals (except the radio, LCD, and CSD blocks, which were shown in Table 1). A typical system application connection diagram is shown in Figure 7.

Figure 7. System Application Connection Diagram



Power

The PSoC 4200_BL device can be supplied from batteries with a voltage range of 1.9 V to 5.5 V by directly connecting to the digital supply (VDDD), analog supply (VDDA), and radio supply (VDDR) pins. Internal LDOs in the device regulate the supply voltage to the required levels for different blocks. The device has one regulator for the digital circuitry and separate regulators for radio circuitry for noise isolation. Analog circuits run directly from the analog supply (VDDA) input. The device uses separate regulators for Deep Sleep and Hibernate (lowered power supply and retention) modes to minimize the power consumption. The radio stops working below 1.9 V, but the device continues to function down to 1.71 V without RF.

Bypass capacitors must be used from VDDx (x = A, D, or R) to ground. The typical practice for systems in this frequency range is to use a capacitor in the 1-µF range in parallel with a smaller capacitor (for example, 0.1 µF). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated to design and obtain optimal bypassing.

Power Supply	Bypass Capacitors
VDDD	The internal bandgap may be bypassed with a 1-µF to 10-µF.
VDDA	0.1-µF ceramic at each pin plus bulk capacitor 1-µF to 10-µF.
VDDR	0.1-µF ceramic at each pin plus bulk capacitor 1-µF to 10-µF.
VCCD	1.3-µF ceramic capacitor at the VCCD pin.
VREF (optional)	The internal bandgap may be bypassed with a 1-µF to 10-µF capacitor.

Development Support

The PSoC 4200_BL family has a rich set of documentation, development tools, and online resources to assist you during your development process. Visit www.cypress.com/go/psoc4ble to find out more.

Documentation

A suite of documentation supports the PSoC 4200_BL family to ensure that you can find answers to your questions quickly. This section contains a list of some of the key documents.

Software User Guide: A step-by-step guide for using PSoC Creator. The software user guide shows you how the PSoC Creator build process works in detail, how to use source control with PSoC Creator, and much more.

Component Datasheets: The flexibility of PSoC allows the creation of new peripherals (Components) long after the device has gone into production. Component datasheets provide all of the information needed to select and use a particular Component, including a functional description, API documentation, example code, and AC/DC specifications.

Application Notes: PSoC application notes discuss a particular application of PSoC in depth; examples include creating standard and custom BLE profiles. Application notes often include example projects in addition to the application note document.

Technical Reference Manual: The Technical Reference Manual (TRM) contains all the technical detail you need to use a PSoC device, including a complete description of all PSoC registers. The TRM is available in the Documentation section at www.cypress.com/psoc4.

Online

In addition to print documentation, the Cypress PSoC forums connect you with fellow PSoC users and experts in PSoC from around the world, 24 hours a day, 7 days a week.

Tools

With industry standard cores, programming, and debugging interfaces, the PSoC 4200_BL family is part of a development tool ecosystem. Visit us at www.cypress.com/go/psoccreator for the latest information on the revolutionary, easy to use PSoC Creator IDE, supported third party compilers, programmers, debuggers, and development kits.

Electrical Specifications

Absolute Maximum Ratings

Table 5. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Analog, digital, or radio supply relative to V_{SS} (V_{SSD} = V_{SSA})	–0.5	–	6	V	Absolute max
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute max
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD} +0.5	V	Absolute max
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	Absolute max
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5	mA	Absolute max, current injected per pin
BID57	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID58	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	–
BID61	LU	Pin current for latch-up	–200	–	200	mA	–

Device-Level Specifications

All specifications are valid for –40 °C ≤ TA ≤ 85 °C and TJ ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 6. DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID6	V_{DD}	Power supply input voltage (V_{DDA} = V_{DDD} = V_{DD})	1.8	–	5.5	V	With regulator enabled
SID7	V_{DD}	Power supply input voltage unregulated (V_{DDA} = V_{DDD} = V_{DD})	1.71	1.8	1.89	V	Internally unregulated Supply
SID8	V_{DDR}	Radio supply voltage (Radio ON)	1.9	–	5.5	V	–
SID8A	V_{DDR}	Radio supply voltage (Radio OFF)	1.71	–	5.5	V	–
SID9	V_{CCD}	Digital regulator output voltage (for core logic)	–	1.8	–	V	–
SID10	C_{VCCD}	Digital regulator output bypass capacitor	1	1.3	1.6	µF	X5R ceramic or better
Active Mode, V_{DD} = 1.71 V to 5.5 V							–
SID13	I_{DD3}	Execute from flash; CPU at 3 MHz	–	2.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID14	I_{DD4}	Execute from flash; CPU at 3 MHz	–	–	–	mA	T = –40 C to 85 °C
SID15	I_{DD5}	Execute from flash; CPU at 6 MHz	–	2.5	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID16	I_{DD6}	Execute from flash; CPU at 6 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID17	I_{DD7}	Execute from flash; CPU at 12 MHz	–	4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID18	I_{DD8}	Execute from flash; CPU at 12 MHz	–	–	–	mA	T = –40 °C to 85 °C

Note
1. Usage above the absolute maximum conditions listed in Table 5 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 6. DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID41	I_{DD31}	GPIO and reset active	–	–	–	nA	T = 25 °C
SID42	I_{DD32}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.8 to 3.6 V							
SID43	I_{DD33}	Stop mode current (V_{DD})	–	20	–	nA	T = 25 °C, V_{DD} = 3.3 V
SID44	I_{DD34}	Stop mode current (V_{DDR})	–	40	–-	nA	T = 25 °C, V_{DDR} = 3.3 V
SID45	I_{DD35}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID46	I_{DD36}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C, V_{DDR} = 1.9 V to 3.6 V
Stop Mode, V_{DD} = 3.6 to 5.5 V							
SID47	I_{DD37}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID48	I_{DD38}	Stop mode current (V_{DDR})	–	–	–	nA	T = 25 °C, V_{DDR} = 5 V
SID49	I_{DD39}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID50	I_{DD40}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID51	I_{DD41}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C
SID52	I_{DD42}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C

Table 7. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	F_{CPU}	CPU frequency	DC	–	48	MHz	1.71 V ≤ V_{DD} ≤ 5.5 V
SID54	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	Guaranteed by characterization
SID55	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	–	25	µs	24-MHz IMO. Guaranteed by characterization.
SID56	$T_{HIBERNATE}$	Wakeup from Hibernate mode	–	–	0.7	ms	Guaranteed by characterization
SID57	T_{STOP}	Wakeup from Stop mode	–	–	2.2	ms	Guaranteed by characterization

Table 9. GPIO AC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83	$F_{GPIOUT2}$	GPIO Fout; 1.7 V≤ V_{DD} ≤ 3.3 V. Fast-Strong mode	–	–	16.7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID84	$F_{GPIOUT3}$	GPIO Fout; 3.3 V ≤ V_{DD} ≤ 5.5 V. Slow-Strong mode	–	–	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID85	$F_{GPIOUT4}$	GPIO Fout; 1.7 V ≤ V_{DD} ≤ 3.3 V. Slow-Strong mode	–	–	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID86	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DD} ≤ 5.5 V	–	–	48	MHz	90/10% V_{IO}

Table 10. OVT GPIO DC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID71A	I_{IL}	Input leakage current (absolute value), V_{IH} > V_{DD}	–	–	10	µA	25 °C, V_{DD} = 0 V, V_{IH}= 3.0 V
SID66A	V_{OL}	Output voltage LOW level	–	–	0.4	V	I_{OL} = 20-mA, V_{DD} > 2.9-V

Table 11. OVT GPIO AC Specifications (P5_0 and P5_1 Only)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID78A	T_{RISE_OVFS}	Output rise time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID79A	T_{FALL_OVFS}	Output fall time in Fast-Strong mode	1.5	–	12	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID80A	T_{RISSS}	Output rise time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID81A	T_{FALLSS}	Output fall time in Slow-Strong mode	10	–	60	ns	25-pF load, 10%–90%, V_{DD}=3.3-V
SID82A	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DD} ≤ 5.5 V Fast-Strong mode	–	–	24	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID83A	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V ≤ V_{DD} ≤ 3.3 V Fast-Strong mode	–	–	16	MHz	90/10%, 25-pF load, 60/40 duty cycle

XRES

Table 12. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID87	V_{IH}	Input voltage HIGH threshold	0.7 × V_{DDD}	–	–	V	CMOS input
SID88	V_{IL}	Input voltage LOW threshold	–	–	0.3 × V_{DDD}	V	CMOS input
SID89	Rpullup	Pull-up resistor	3.5	5.6	8.5	kΩ	–
SID90	C_{IN}	Input capacitance	–	3	–	pF	–
SID91	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	–
SID92	I_{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	–

Table 14. Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID122	V_{N3}	Input referred, 10-kHz, power = high	–	28	–	nV/rtHz	–
SID123	V_{N4}	Input referred, 100-kHz, power = high	–	15	–	nV/rtHz	–
SID124	C_{LOAD}	Stable up to maximum load. Performance specs at 50 pF	–	–	125	pF	–
SID125	Slew_rate	Cload = 50 pF, Power = High, $V_{DDA} \geq 2.7$ V	6	–	–	V/µsec	–
SID126	T_op_wake	From disable to enable, no external RC dominating	–	300	–	µsec	–
Comp_mode (Comparator Mode; 50-mV Drive, $T_{RISE} = T_{FALL}$ (Approx.)							
SID127	T_{PD1}	Response time; power = high	–	150	–	nsec	–
SID128	T_{PD2}	Response time; power = medium	–	400	–	nsec	–
SID129	T_{PD3}	Response time; power = low	–	2000	–	nsec	–
SID130	Vhyst_op	Hysteresis	–	10	–	mV	–
Deep Sleep (Deep Sleep mode operation is only guaranteed for $V_{DDA} > 2.5$ V)							
SID131	GBW_DS	Gain bandwidth product	–	50	–	kHz	–
SID132	IDD_DS	Current	–	15	–	µA	–
SID133	Vos_DS	Offset voltage	–	5	–	mV	–
SID134	Vos_dr_DS	Offset voltage drift	–	20	–	µV/°C	–
SID135	Vout_DS	Output voltage	0.2	–	V_{DD}–0.2	V	–
SID136	Vcm_DS	Common mode voltage	0.2	–	V_{DD}–1.8	V	–

Table 15. Comparator DC Specifications[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID140	$V_{OFFSET1}$	Input offset voltage, Factory trim	–	–	±10	mV	–
SID141	$V_{OFFSET2}$	Input offset voltage, Custom trim	–	–	±6	mV	–
SID141A	$V_{OFFSET3}$	Input offset voltage, ultra-low-power mode	–	±12	–	mV	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID142	V_{HYST}	Hysteresis when enabled. Common Mode voltage range from 0 to VDD –1	–	10	35	mV	–
SID143	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} –0.1	V	Modes 1 and 2
SID144	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}	V	–
SID145	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} –1.15	V	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID146	CMRR	Common mode rejection ratio	50	–	–	dB	$V_{DDD} \geq 2.7$ V
SID147	CMRR	Common mode rejection ratio	42	–	–	dB	$V_{DDD} \leq 2.7$ V
SID148	I_{CMP1}	Block current, normal mode	–	–	400	µA	–
SID149	I_{CMP2}	Block current, low power mode	–	–	100	µA	–

Note
3. ULP LCOMP operating conditions:
   - V_{DDD} 2.6 V-5.5 V for datasheet temp range < 0 °C
   - V_{DDD} 1.8 V-5.5 V for datasheet temp range ≥ 0 °C

Table 19. SAR ADC AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID167	A_psrr	Power supply rejection ratio	70	–	–	dB	Measured at 1-V reference
SID168	A_cmrr	Common mode rejection ratio	66	–	–	dB	–
SID169	A_samp	Sample rate	–	–	1	Msps	
SID313	Fsarintref	SAR operating speed without external ref. bypass	–	–	100	Ksps	12-bit resolution
SID170	A_snr	Signal-to-noise ratio (SNR)	65	–	–	dB	Fin = 10 kHz
SID171	A_bw	Input bandwidth without aliasing	–	–	A_samp/2	kHz	–
SID172	A_inl	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1.7	–	2	LSB	Vref = 1 V to V_{DD}
SID173	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6 V, 1 Msps	–1.5	–	1.7	LSB	Vref = 1.71 V to V_{DD}
SID174	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1.5	–	1.7	LSB	Vref = 1 V to V_{DD}
SID175	A_dnl	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 1 Msps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID176	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6 V, 1 Msps	–1	–	2	LSB	Vref = 1.71 V to V_{DD}
SID177	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5 V, 500 Ksps	–1	–	2.2	LSB	Vref = 1 V to V_{DD}
SID178	A_thd	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz

CSD

Table 20. CSD Block Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID179	V_{CSD}	Voltage range of operation	1.71	–	5.5	V	–
SID180	IDAC1	DNL for 8-bit resolution	–1	–	1	LSB	–
SID181	IDAC1	INL for 8-bit resolution	–3	–	3	LSB	–
SID182	IDAC2	DNL for 7-bit resolution	–1	–	1	LSB	–
SID183	IDAC2	INL for 7-bit resolution	–3	–	3	LSB	–
SID184	SNR	Ratio of counts of finger to noise	5	–	–	Ratio	Capacitance range of 9 to 35 pF, 0.1 pF sensitivity. Radio is not operating during the scan
SID185	I_{DAC1_CRT1}	Output current of IDAC1 (8 bits) in High range	–	612	–	µA	–
SID186	I_{DAC1_CRT2}	Output current of IDAC1 (8 bits) in Low range	–	306	–	µA	–
SID187	I_{DAC2_CRT1}	Output current of IDAC2 (7 bits) in High range	–	305	–	µA	–
SID188	I_{DAC2_CRT2}	Output current of IDAC2 (7 bits) in Low range	–	153	–	µA	–

Table 32. Fixed UART AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID236	F_{UART}	Bit rate	–	–	1	Mbps	–

SPI Specifications

Table 33. Fixed SPI DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID237	I_{SPI1}	Block current consumption at 1 Mbps	–	–	360	µA	–
SID238	I_{SPI2}	Block current consumption at 4 Mbps	–	–	560	µA	–
SID239	I_{SPI3}	Block current consumption at 8 Mbps	–	–	600	µA	–

Table 34. Fixed SPI AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID240	F_{SPI}	SPI operating frequency (master; 6X oversampling)	–	–	8	MHz	–

Table 35. Fixed SPI Master Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID241	T_{DMO}	MOSI valid after Sclock driving edge	–	–	18	ns	–
SID242	T_{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO sampling used	20	–	–	ns	Full clock, late MISO sampling
SID243	T_{HMO}	Previous MOSI data hold time	0	–	–	ns	Referred to Slave capturing edge

Table 36. Fixed SPI Slave Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID244	T_{DMI}	MOSI valid before Sclock capturing edge	40	–	–	ns	–
SID245	T_{DSO}	MISO valid after Sclock driving edge	–	–	$42 + 3 \times T_{CPU}$	ns	–
SID246	T_{DSO_ext}	MISO valid after Sclock driving edge in external clock mode	–	–	53	ns	$V_{DD} < 3.0$ V
SID247	T_{HSO}	Previous MISO data hold time	0	–	–	ns	–
SID248	$T_{SSELSCK}$	SSEL valid to first SCK valid edge	100	–	–	ns	–

Memory

Table 37. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID249	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–
SID309	T_{WS48}	Number of Wait states at 32–48 MHz	2	–	–		CPU execution from flash
SID310	T_{WS32}	Number of Wait states at 16–32 MHz	1	–	–		CPU execution from flash
SID311	T_{WS16}	Number of Wait states for 0–16 MHz	0	–	–		CPU execution from flash

Table 38. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID250	$T_{ROWWRITE}$[5]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes for 128 KB flash devices Row (block) = 256 bytes for 256 KB flash devices
SID251	$T_{ROWERASE}$[5]	Row erase time	–	–	13	ms	–
SID252	$T_{ROWPROGRAM}$[5]	Row program time after erase	–	–	7	ms	–
SID253	$T_{BULKERASE}$[5]	Bulk erase time (256 KB)	–	–	35	ms	–
SID254	$T_{DEVPROG}$[5]	Total device program time	–	–	50	seconds	256 KB
SID254A			–	–	25		128 KB
SID255	F_{END}	Flash endurance	100 K	–	–	cycles	–
SID256	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	years	–
SID257	F_{RET2}	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–	years	–

System Resources

Power-on-Reset (POR)

Table 39. POR DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID258	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.45	V	–
SID259	$V_{FALLIPOR}$	Falling trip voltage	0.75	–	1.40	V	–
SID260	$V_{IPORHYST}$	Hysteresis	15	–	200	mV	–

Table 40. POR AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID264	T_{PPOR_TR}	PPOR response time in Active and Sleep modes	–	–	1	µs	–

Table 41. Brown-Out Detect

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID261	$V_{FALLPPOR}$	BOD trip voltage in Active and Sleep modes	1.64	–	–	V	–
SID262	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep mode	1.4	–	–	V	–

Table 42. Hibernate Reset

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID263	$V_{HBRTRIP}$	BOD trip voltage in Hibernate mode	1.1	–	–	V	–

Note

5. It can take as much as 20 milliseconds to write to flash. During this time, the device should not be reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.

Table 52. BLE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID378	ITX,-6dBm	TX current at –6-dBm setting (PA3)	–	14.5	–	mA	–
SID379	ITX,-12dBm	TX current at –12-dBm setting (PA2)	–	13.2	–	mA	–
SID380	ITX,-18dBm	TX current at –18-dBm setting (PA1)	–	12.5	–	mA	–
SID380A	Iavg_1sec, 0dBm	Average current at 1-second BLE connection interval	–	17.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
SID380B	Iavg_4sec, 0dBm	Average current at 4-second BLE connection interval	–	6.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
General RF Specifications							
SID381	FREQ	RF operating frequency	2400	–	2482	MHz	–
SID382	CHBW	Channel spacing	–	2	–	MHz	–
SID383	DR	On-air data rate	–	1000	–	kbps	–
SID384	IDLE2TX	BLE.IDLE to BLE. TX transition time	–	120	140	µs	–
SID385	IDLE2RX	BLE.IDLE to BLE. RX transition time	–	75	120	µs	–
RSSI Specifications							
SID386	RSSI, ACC	RSSI accuracy	–	±5	–	dB	–
SID387	RSSI, RES	RSSI resolution	–	1	–	dB	–
SID388	RSSI, PER	RSSI sample period	–	6	–	µs	–

Table 53. ECO Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID389	F_{ECO}	Crystal frequency	–	24	–	MHz	–
SID390	F_{TOL}	Frequency tolerance	–50	–	50	ppm	–
SID391	ESR	Equivalent series resistance	–	–	60	Ω	–
SID392	PD	Drive level	–	–	100	µW	–
SID393	T_{START1}	Startup time (Fast Charge on)	–	–	850	µs	–
SID394	T_{START2}	Startup time (Fast Charge off)	–	–	3	ms	–
SID395	C_L	Load capacitance	–	8	–	pF	–
SID396	C0	Shunt capacitance	–	1.1	–	pF	–
SID397	I_{ECO}	Operating current	–	1400	–	µA	–

Ordering Information

The PSoC 4200_BL part numbers and features are listed in Table 55.

Table 55. PSoC 4200_BL Part Numbers

Product Family	MPN	Max CPU Speed (MHz)	BLE subsystem	Flash (KB)	SRAM (KB)	UDB	Opamp	CapSense	TMG (Gestures)	Direct LCD Drive	12-bit SAR ADC	DMA	LP Comparators	TCPWM Blocks	SCB Blocks	GPIO	Package	Temperature Range
PSoC 4200_BL	CY8C4247LQI-BL473	48	4.1	128	16	4	4	–	–	–	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247FNI-BL473	48	4.1	128	16	4	4	–	–	–	1 Msps	–	2	4	2	36	CSP	85 °C
	CY8C4247LQI-BL453	48	4.1	128	16	4	4	1	–	–	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL463	48	4.1	128	16	4	4	–	–	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247LQI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	QFN	85 °C
	CY8C4247FNI-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	68-CSP	85 °C
	CY8C4247FNI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	68-CSP	85 °C
	CY8C4247FNQ-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	68-CSP	105 °C
	CY8C4247LQQ-BL483	48	4.1	128	16	4	4	1	–	1	1 Msps	–	2	4	2	36	QFN	105 °C
	CY8C4247FLI-BL493	48	4.1	128	16	4	4	1	1	1	1 Msps	–	2	4	2	36	Thin 68-CSP	85 °C
	CY8C4248LQI-BL473	48	4.1	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248LQI-BL453	48	4.1	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248LQI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248FLI-BL483	48	4.1	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	Thin 76-CSP	85 °C
	CY8C4248LQI-BL543	48	4.2	256	32	–	2	–	–	–	1 Msps	1	–	4	2	36	QFN	85 °C
	CY8C4248FNI-BL543	48	4.2	256	32	–	2	–	–	–	1 Msps	1	–	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL573	48	4.2	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL573	48	4.2	256	32	4	4	–	–	–	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL553	48	4.2	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL553	48	4.2	256	32	4	4	1	–	–	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL563	48	4.2	256	32	4	4	–	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL563	48	4.2	256	32	4	4	–	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248LQI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	85 °C
	CY8C4248FLI-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	Thin 76-CSP	85 °C
	CY8C4248LQQ-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	QFN	105 °C
	CY8C4248FNQ-BL583	48	4.2	256	32	4	4	1	–	1	1 Msps	1	2	4	2	36	76-CSP	105 °C
	CY8C4248LQI-BL593	48	4.2	256	32	4	4	1	1	1	1 Msps	1	2	4	2	36	QFN	85 °C
	CY8C4248FNI-BL593	48	4.2	256	32	4	4	1	1	1	1 Msps	1	2	4	2	36	76-CSP	85 °C

Packaging

Table 56. Package Characteristics

Parameter	Description	Conditions	Min	Typ	Max	Units
T_A	Operating ambient temperature	–	–40	25.00	105	°C
T_J	Operating junction temperature	–	–40	–	125	°C
T_{JA}	Package θ_{JA} (56-pin QFN)	–	–	16.9	–	°C/watt
T_{JC}	Package θ_{JC} (56-pin QFN)	–	–	9.7	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball WLCSP)	–	–	20.1	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball WLCSP)	–	–	0.19	–	°C/watt
T_{JA}	Package θ_{JA} (76-ball Thin WLCSP)	–	–	20.9	–	°C/watt
T_{JC}	Package θ_{JC} (76-ball Thin WLCSP)	–	–	0.17	–	°C/watt
T_{JA}	Package θ_{JA} (68-ball WLCSP)		–	16.6	–	°C/watt
T_{JC}	Package θ_{JC} (68-ball WLCSP)		–	0.19	–	°C/watt
T_{JA}	Package θ_{JA} (68-ball Thin WLCSP)		–	16.6	–	°C/watt
T_{JC}	Package θ_{JC} (68-ball Thin WLCSP)		–	0.19	–	°C/watt

Table 57. Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All packages	260 °C	30 seconds

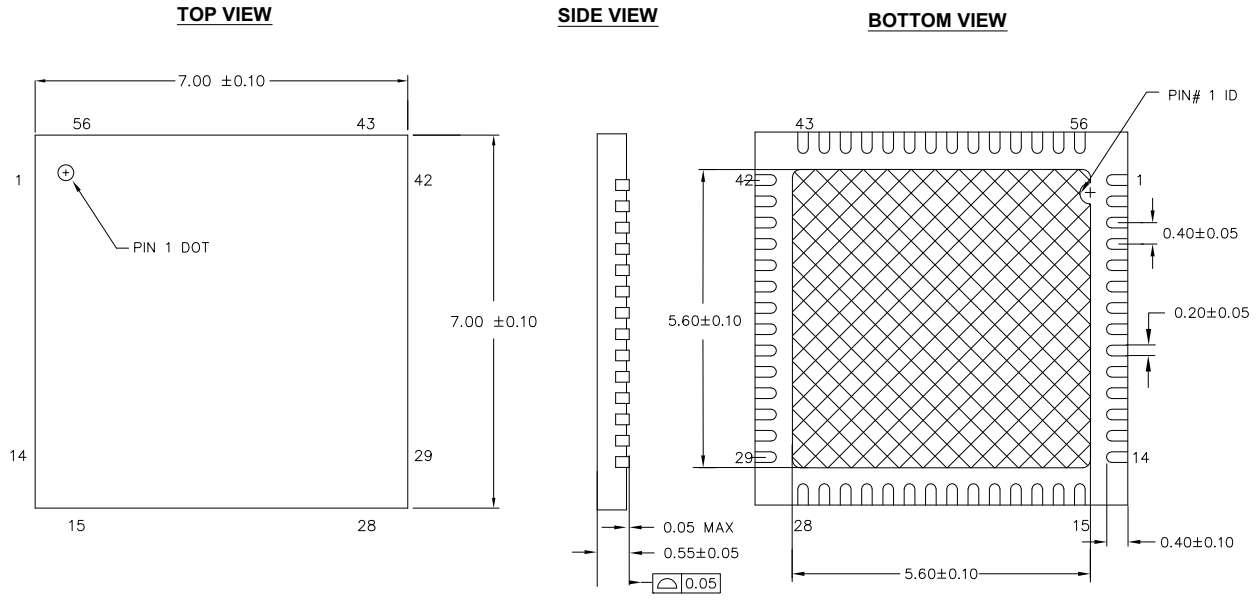
Table 58. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
56-pin QFN	MSL 3
All WLCSP packages	MSL 1

Table 59. Package Details

Spec ID	Package	Description
001-58740 Rev. *C	56-pin QFN	7.0 mm × 7.0 mm × 0.6 mm
001-96603 Rev. *A	76-ball WLCSP	4.04 mm × 3.87 mm × 0.55 mm
002-10658, Rev. **	76-ball thin WLCSP	4.04 mm × 3.87 mm × 0.4 mm
001-92343 Rev. *A	68-ball WLCSP	3.52 mm × 3.91 mm × 0.55 mm
001-99408 Rev **	68-ball Thin WLCSP	52 mm × 3.91 mm × 0.4 mm

Figure 8. 56-Pin QFN 7 × 7 × 0.6 mm



NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. BASED ON REF JEDEC # MO-248
3. ALL DIMENSIONS ARE IN MILLIMETERS

001-58740 *C

The center pad on the QFN package should be connected to ground (VSS) for best mechanical, thermal, and electrical performance.

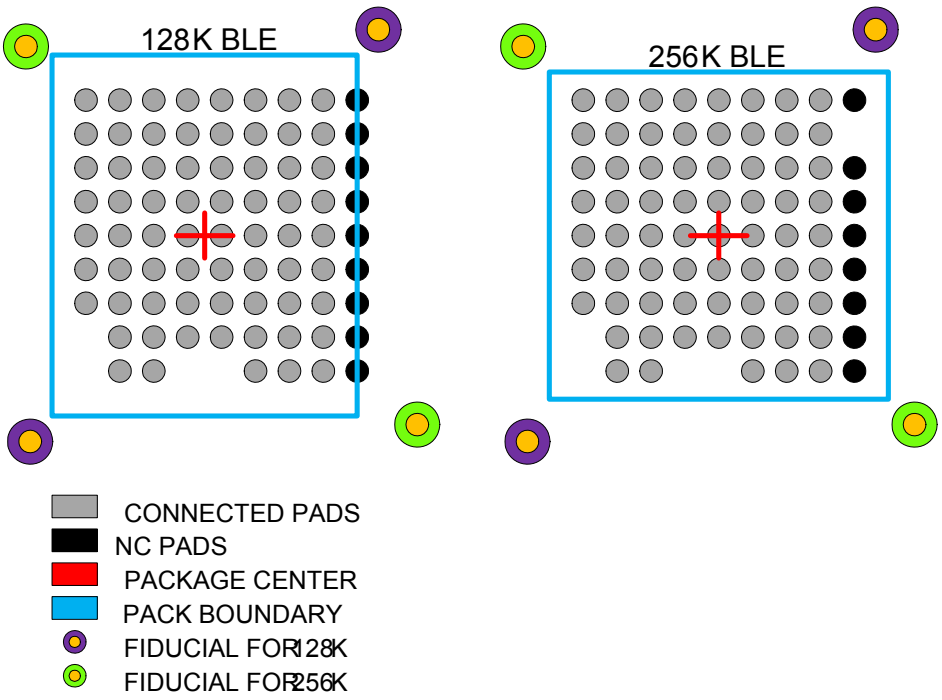
WLCSP Compatibility

The PSoC 4XXX_BLE family has products with 128 KB (16KB SRAM) and 256 KB (32KB SRAM) Flash. Package pin-outs and sizes are identical for the 56-pin QFN package but are different in one dimension for the 68-ball WLCSP.

The 256KB Flash product has an extra column of balls which are required for mechanical integrity purposes in the Chip-Scale package. With consideration for this difference, the land pattern on the PCB may be designed such that either product may be used with no change to the PCB design.

Figure 9 shows the 128KB and 256 KB Flash CSP packages.

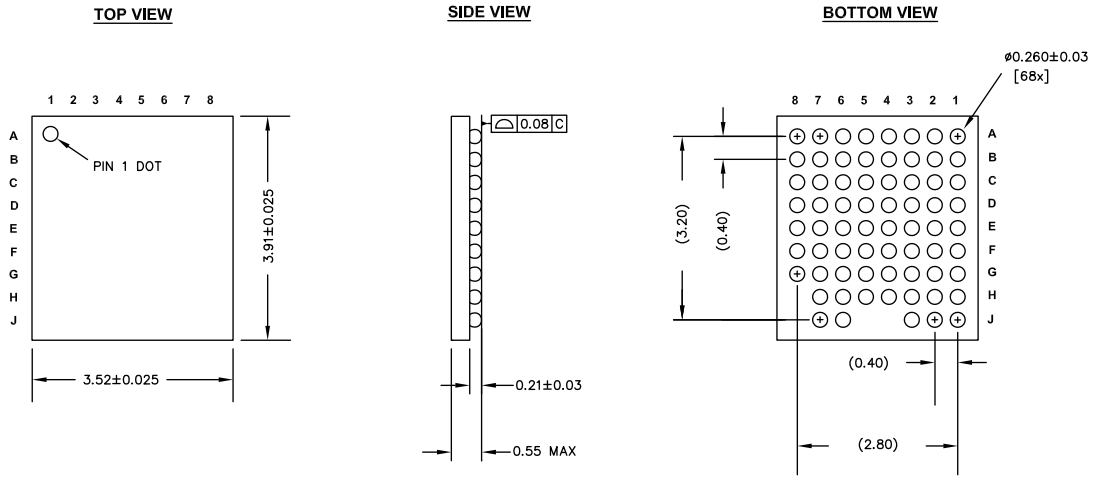
Figure 9. 128KB and 256 KB Flash CSP Packages



The rightmost column of (all NC, No Connect) balls in the 256K BLE WLCSP is for mechanical integrity purposes. The package is thus wider (3.2 mm versus 2.8 mm). All other dimensions are identical. Cypress will provide layout symbols for PCB layout.

The scheme in Figure 9 is implemented to design the PCB for the 256K BLE package with the appropriate space requirements thus allowing use of either package at a later time without redesigning the Printed Circuit Board.

Figure 10. 68-Ball WLCSP Package Outline

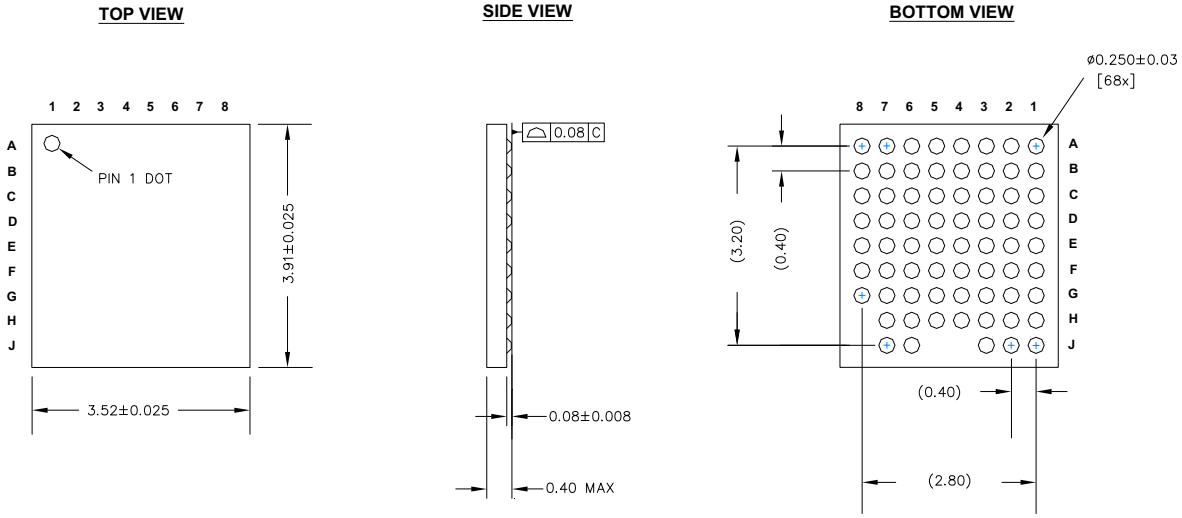


NOTES:

1. REFERENCE JEDEC PUBLICATION 95, DESIGN GUIDE 4.18
2. ALL DIMENSIONS ARE IN MILLIMETERS

001-92343 *A

Figure 11. 68-Ball Thin WLCSP

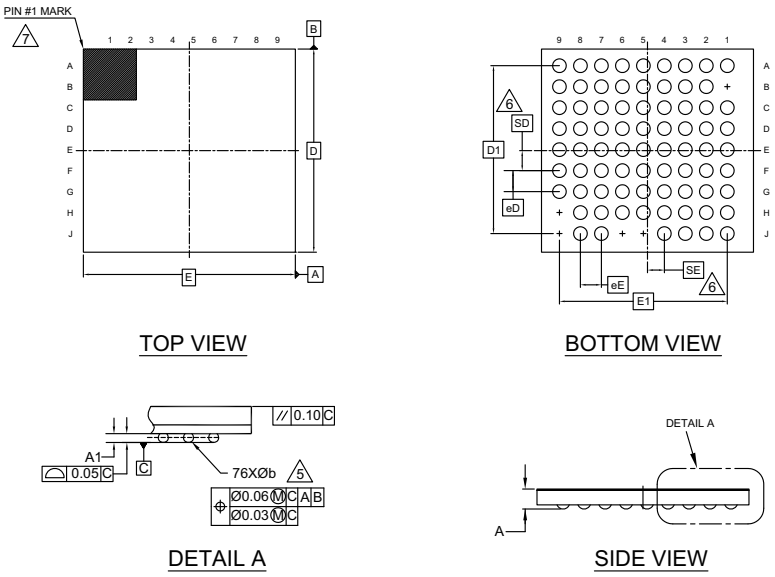


NOTES:

1. REFERENCE JEDEC PUBLICATION 95, DESIGN GUIDE 4.18
2. ALL DIMENSIONS ARE IN MILLIMETERS

001-99408 **

Figure 12. 76-Ball WLCSP Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	0.55
A1	0.18	0.21	0.24
D	3.87 BSC		
E	4.04 BSC		
D1	3.20 BSC		
E1	3.20 BSC		
MD	9		
ME	9		
N	76		
Ø b	0.23	0.26	0.29
eD	0.40 BSC		
eE	0.40 BSC		
SD	0.381 BSC		
SE	0.321 BSC		

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.
9. JEDEC SPECIFICATION NO. REF : N/A

001-96603 *B

Revision History

Description Title: PSoC® 4: 4200_BLE Family Datasheet Programmable System-on-Chip (PSoC®) Document Number: 002-23053				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	6078076	PMAD/ WKA	02/22/2018	New datasheet